

Silicon PNP Power Transistors

BD244/A/B/C

DESCRIPTION

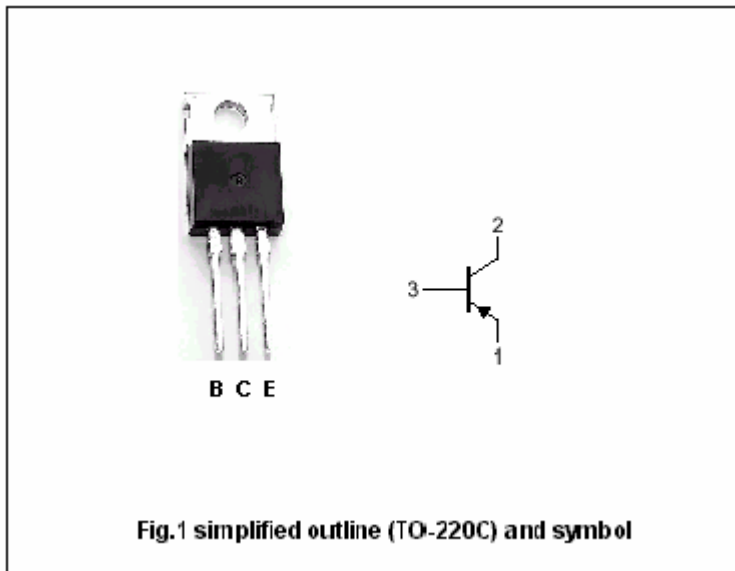
- With TO-220C package
- Complement to type BD243/A/B/C

APPLICATIONS

- For medium power linear and switching applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Emitter |
| 2 | Collector;connected to mounting base |
| 3 | Base |



Absolute maximum ratings (Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | BD244 | -45 | V |
| | | BD244A | -60 | |
| | | BD244B | -80 | |
| | | BD244C | -100 | |
| V _{CEO} | Collector-emitter voltage | BD244 | -45 | V |
| | | BD244A | -60 | |
| | | BD244B | -80 | |
| | | BD244C | -100 | |
| V _{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I _C | Collector current | | -6 | A |
| I _{CM} | Collector current-peak | | -10 | A |
| I _B | Base current | | -2 | A |
| P _C | Collector power dissipation | T _C =25°C | 65 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -65~150 | °C |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | |
|-----------------------|--------------------------------------|---|--|------|------|------|----|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | BD244 | -45 | | | V | |
| | | BD244A | -60 | | | | |
| | | BD244B | -80 | | | | |
| | | BD244C | -100 | | | | |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-6A; I _B =-1 A | | | -1.5 | V | |
| V _{BE} | Base-emitter on voltage | I _C =-6A; V _{CE} =-4V | | | -2.0 | V | |
| I _{CEO} | Collector cut-off current | BD244/A | V _{CE} =-30V; I _B =0 | | | -0.7 | mA |
| | | BD244B/C | V _{CE} =-60V; I _B =0 | | | | |
| I _{CES} | Collector cut-off current | BD244 | V _{CE} =-45V; V _{BE} =0 | | | -0.4 | mA |
| | | BD244A | V _{CE} =-60V; V _{BE} =0 | | | | |
| | | BD244B | V _{CE} =-80V; V _{BE} =0 | | | | |
| | | BD244C | V _{CE} =-100V; V _{BE} =0 | | | | |
| I _{EBO} | Emitter cut-off current | V _{EB} =-5V; I _C =0 | | | 1 | mA | |
| h _{FE-1} | DC current gain | I _C =-0.3A; V _{CE} =-4V | 30 | | | | |
| h _{FE-2} | DC current gain | I _C =-3A; V _{CE} =-4V | 15 | | | | |

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PACKAGE OUTLINE

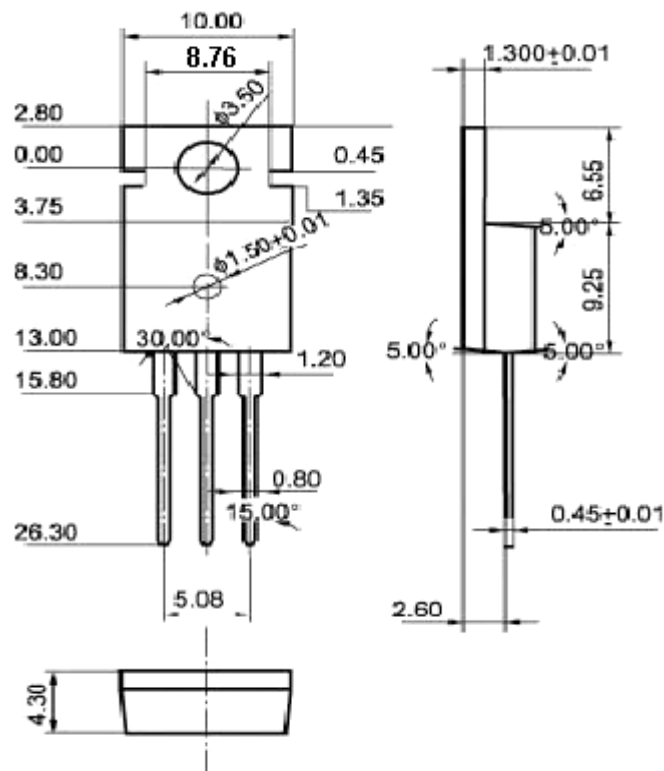


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)